

Schottky barrier diode

RB411D

●Applications

Low power rectification
For switching power supply

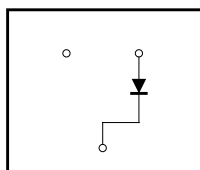
●Features

- 1) Small surface mounting type. (SMD3)
- 2) Low V_F . ($V_F=0.43V$ Typ. at 0.5A)
- 3) High reliability.

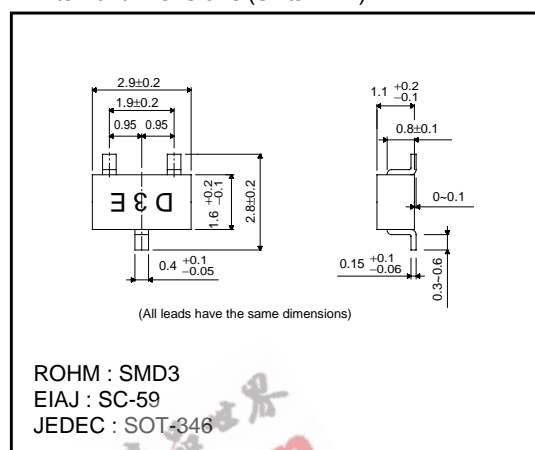
●Construction

Silicon epitaxial planar

●Circuit



●External dimensions (Units : mm)



●Absolute maximum ratings (Ta = 25°C)

Parameter	Symbol	Limits	Unit
Peak reverse voltage	V_{RM}	40	V
DC reverse voltage	V_R	20	V
Mean rectifying current	I_o	0.5	A
Peak forward surge current *	I_{FSM}	3	A
Junction temperature	T_j	125	°C
Storage temperature	T_{stg}	-40~+125	°C

* 60Hz for 1 μ s

●Electrical characteristics (Ta = 25°C)

Parameter	Symbol	Min.	Typ.	Max.	Unit	Conditions
Forward voltage	V_{F1}	-	-	0.3	V	$I_F=10mA$
Forward voltage	V_{F2}	-	-	0.5	V	$I_F=500mA$
Reverse current	I_R	-	-	30	μA	$V_R=10V$
Capacitance between terminals	C_T	-	20	-	pF	$V_R=10V, f=1MHz$

Note) sensitive product handling required.

Diodes

●Electrical characteristic curves (Ta = 25°C)

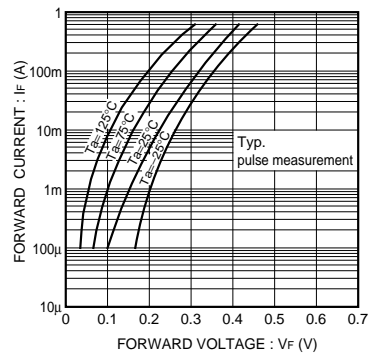


Fig. 1 Forward characteristics

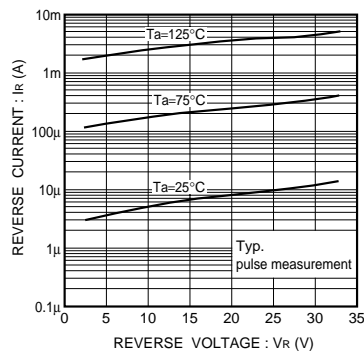


Fig. 2 Reverse characteristics

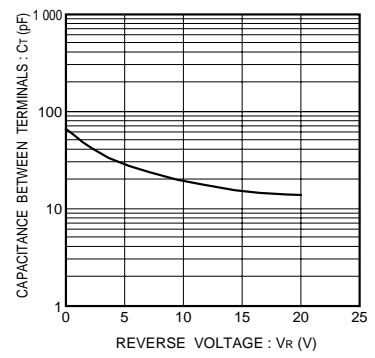


Fig. 3 Capacitance between terminals characteristic

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